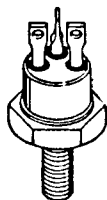


SFT5001 5 AMP HIGH SPEED PNP TRANSISTOR 150 VOLTS	X00147 SSDI 14849 FIRESTONE BLVD. LA MIRADA, CA. 90638 (213) 921-9660 FAX (213) 921-2396
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CASE STYLE X
JEDEC TO-59
ALL TERMINALS ISOLATED FROM CASE



FEATURES

- ▶ RADIATION TOLERANT
- ▶ SUPERIOR TO JEDEC 2N5001 SERIES
- ▶ HIGH FREQUENCY, TYPICAL f_T 100MHz
- ▶ VERY LOW SATURATION
- ▶ FAST SWITCHING, 130 NSEC MAX t_{on}
- ▶ DESIGNED FOR COMPLIMENTARY USE WITH SFT3997

MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	VCEO	80	Volts
Collector-Base Voltage	VCBO	150	Volts
Emitter-Base Voltage	VEBO	8	Volts
Collector Current	IC	5	Amps
Base Current	IB	1	Amps
Total Device Dissipation @ $T_c = 100^\circ\text{C}$ Derate Above 100°C	PD	30 300	Watts mW/ $^\circ\text{C}$
Operating and Storage Temperature	TJ, Tstg	-65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case	R θ JC	3.33	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

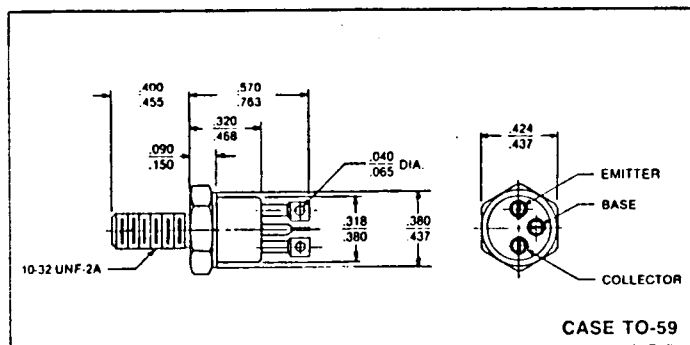
Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage* (IC = 10mA _{dc})	BVCEO	80		Volts
Collector-Base Breakdown Voltage (IC = 20 μ A _{dc})	BVCBO	150		Volts

ELECTRICAL CHARACTERISTICS

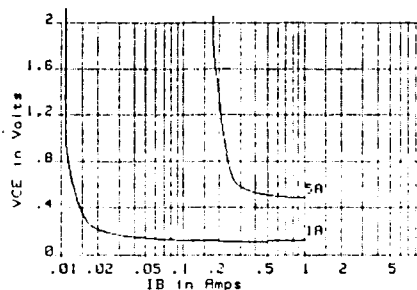
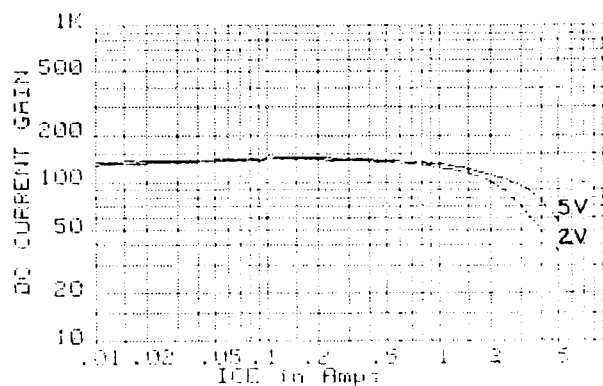
Characteristics		Symbol	Min	Max	Unit
Emitter-Base Breakdown Voltage ($I_E = 20 \mu A$)		BVEBO	8		Vdc
Collector Cutoff Current (VCB = 100 Vdc, VCE = 40 Vdc)		ICBO ICEO		1.0 10	μA μA
Emitter Cutoff Current (VEB = 6 Vdc)		IEBO		1.0	μA
DC Current Gain* ($I_C = 50 mA$, VCE = 5 Vdc) ($I_C = 1.0 A$, VCE = 5 Vdc) ($I_C = 1.0 A$, VCE = 5 Vdc)		hFE	50 50 30		
Collector-Emitter Saturation Voltage* ($I_C = 1.0 A$, $I_B = 100 mA$) ($I_C = 5.0 A$, $I_B = 500 mA$)		VCE(SAT)		500 1.0	mVdc Vdc
Base-Emitter Saturation Voltage ($I_C = 1.0 A$, $I_B = 100 mA$) ($I_C = 5.0 A$, $I_B = 500 mA$)		VBE(SAT)		900 1.0	mVdc Vdc
Current Gain Bandwidth Product ($I_C = 500 mA$, VCE = 5 Vdc, $f = 10 MHz$)		fT	80		MHz
Output Capacitance (VCB = 10 Vdc, $I_E = 0 A$, $f = 1.0 MHz$)		Cob		100	pf
Delay Time	(VCC = 20 Vdc, $I_C = 1.0 A$, $I_{B1} = I_{B2} = 100 mA$, VBE (off) = 3.7 Vdc, RL = 20 Ω)	t(on)		150	ns
Rise Time					
Storage Time		t(off)		500	ns
Fall Time					

*Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%

PHYSICAL DIMENSIONS



TYPICAL OPERATING CURVES



SSDI

SOLID STATE DEVICES, INC.

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